

Application Specific Discretes A.S.D.

TRANSIL ARRAY FOR ESD PROTECTION

APPLICATIONS

Where transient overvoltage protection in ESD sensitive equipment is required, such as:

- COMPUTERS
- PRINTERS
- COMMUNICATION SYSTEMS
- GSM HANDSETS AND ACCESSORIES
- CAR RADIO

It is particulary recommended for parallel port protection where the line interface withstands only 2 kV ESD surge.

FEATURES

- 6 UNIDIRECTIONAL TRANSIL FUNCTIONS
- LOW LEAKAGE CURRENT: I_R max. < 2 µA
- 200 W PEAK PULSE POWER (8/20 µs)

DESCRITION

The ESDA6V1U1 is a monolithic voltage suppressor designed to protect components which are connected to data and transmission lines against ESD.

It clamps the voltage just above the logic level supply for positive transients, and to a diode drop below ground for negative transients.

BENEFITS

High ESD protection level : up to 25 kV

High integration

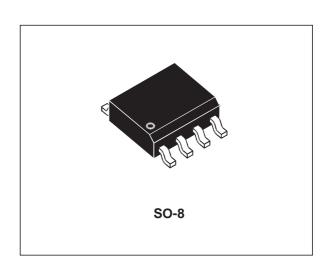
Suitable for high density boards

COMPLIES WITH THE FOLLOWING STANDARDS:

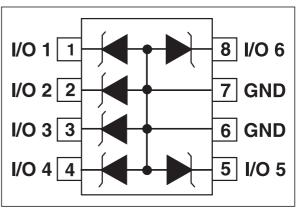
IEC61000-4-2: level 4

MIL STD 883C-Method 3015-6: class3

(human body model)



FUNCTIONAL DIAGRAM



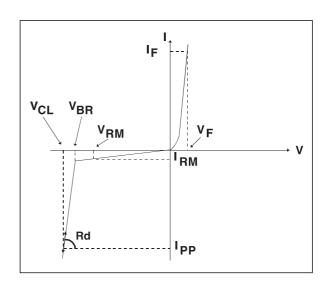
August 2002 - Ed: 3A 1/6

ABSOLUTE MAXIMUM RATINGS (Tamb = 25°C)

Symbol	Parameter	Value	Unit
V _{PP}	Electrostatic discharge MIL STD 883C - Method 3015-6	25	kV
P _{PP}	Peak pulse power (8/20μs)	200	W
T _{stg} T _j	Storage temperature range Maximum junction temperature	- 55 to + 150 125	°C °C
TL	Maximum lead temperature for soldering during 10s	260	∘C

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C)

Symbol	Parameter				
V_{RM}	Stand-off voltage				
V_{BR}	Breakdown voltage				
V_{CL}	Clamping voltage				
I _{RM}	Leakage current				
I _{PP}	Peak pulse current				
αΤ	Voltage temperature coefficient				
С	Capacitance				
Rd	Dynamic resistance				
V _F	Forward voltage drop				



Types	V _{BR}		I _R	I _{RM} @	V _{RM}	Rd	αΤ	С	V _F @	D IF
	min.	max.		max.		typ.	max.	typ.	max.	
						note 1	note 2	0V bias		
	V	V	mA	μА	V	Ω	10 ⁻⁴ /°C	pF	V	mA
ESDA6V1U1	6.1	7.2	1	2	5	0.5	6	100	1.5	200

 $\begin{array}{l} \textbf{note 1}: \mbox{Square pulse, lpp} = 25\mbox{A, tp=}2.5\mbox{\mu s.} \\ \textbf{note 2}: \ \Delta\mbox{ V}_{BR} = \mbox{\alpha}\mbox{T}^* \mbox{ (Tamb } \text{-}25\mbox{°C}) * \mbox{ V}_{BR} \mbox{ (25\mbox{°C})} \\ \end{array}$

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CALCULATION OF THE CLAMPING VOLTAGE

USE OF THE DYNAMIC RESISTANCE

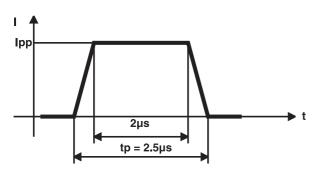
The ESDA family has been designed to clamp fast spikes like ESD. Generally the PCB designers need to calculate easily the clamping voltage V_{CL} . This is why we give the dynamic resistance in addition to the classical parameters. The voltage across the protection cell can be calculated with the following formula:

$$V_{CL} = V_{BR} + Rd I_{PP}$$

Where Ipp is the peak current through the ESDA cell.

DYNAMIC RESISTANCE MEASUREMENT

The short duration of the ESD has led us to prefer a more adapted test wave, as below defined, to the classical 8/20µs and 10/1000µs surges.



2.5µs duration measurement wave.

As the value of the dynamic resistance remains stable for a surge duration lower than 20µs, the 2.5µs rectangular surge is well adapted. In addition both rise and fall times are optimized to avoid any parasitic phenomenon during the measurement of Rd.

Fig. 1: Peak power dissipation versus initial junction temperature.

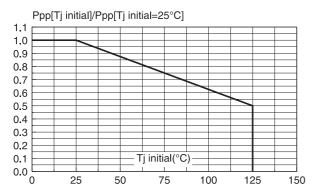


Fig. 2: Peak pulse power versus exponential pulse duration (Tj initial = 25 °C).

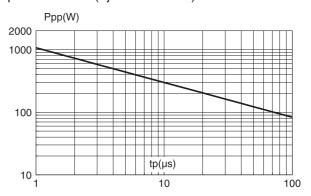


Fig. 3: Clamping voltage versus peak pulse current (Tj initial = 25 °C).

Rectangular waveform tp = $2.5 \mu s$.

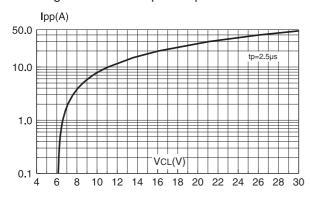


Fig. 4: Capacitance versus reverse applied voltage (typical values).

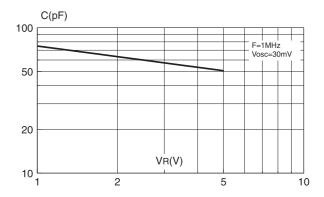


Fig. 5: Relative variation of leakage current versus junction temperature (typical values).

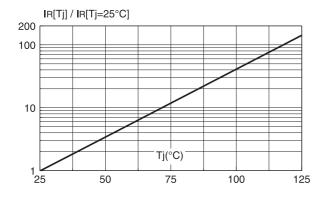
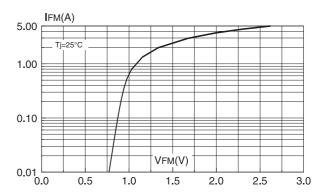
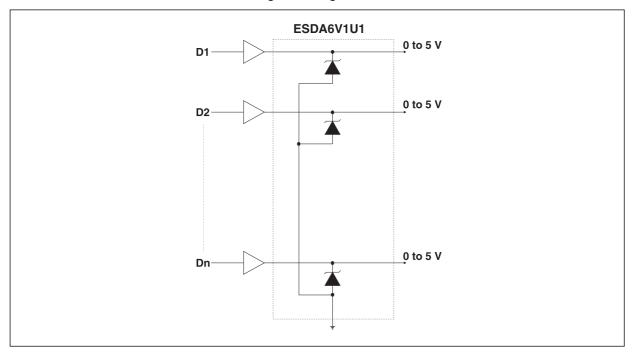


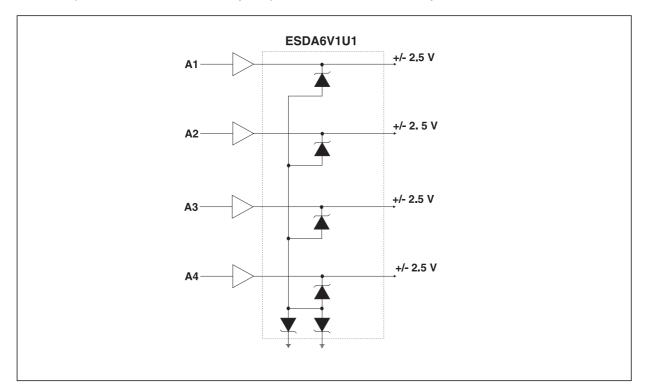
Fig. 6: Peak forward voltage drop versus peak forward current (typical values).



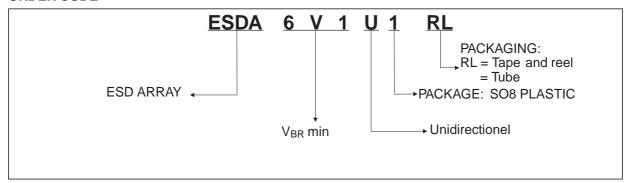
APPLICATION EXAMPLE: Protection of logic-level signals.



APPLICATION EXAMPLE : Protection of symmetrical signals. **Note :** Capacitance value between any I/O pin and Ground is divided by 2.



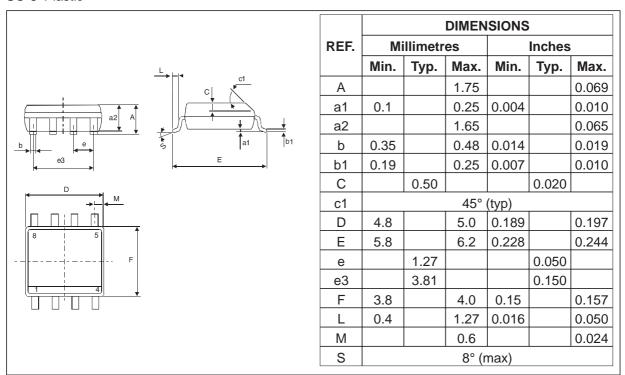
ORDER CODE



MARKING: Logo, Date Code, E6V1U1

PACKAGE MECHANICAL DATA

SO-8 Plastic



Packaging: Preferred packaging is tape and reel.

Weight: 0.08g.

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